

7MBR25XKA120-50

IGBT Modules

Power Module(X series)
1200V / 25A / PIM

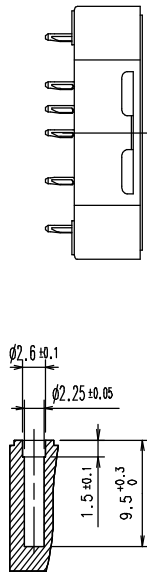
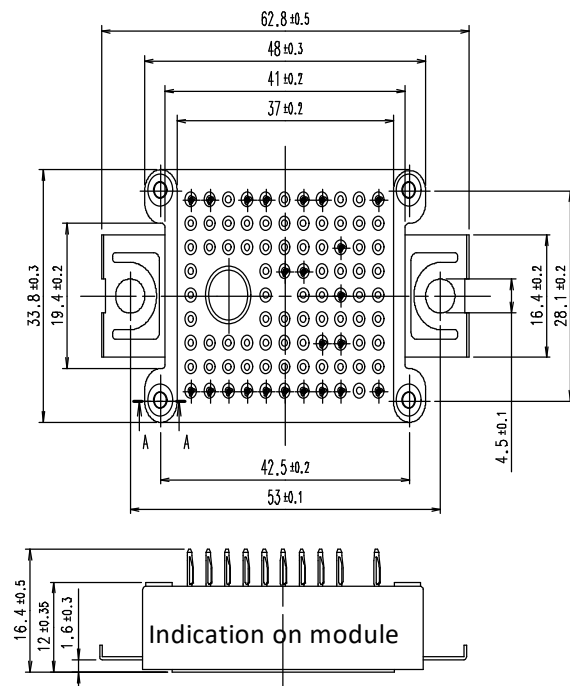
■ **Features**

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant Product

■ **Applications**

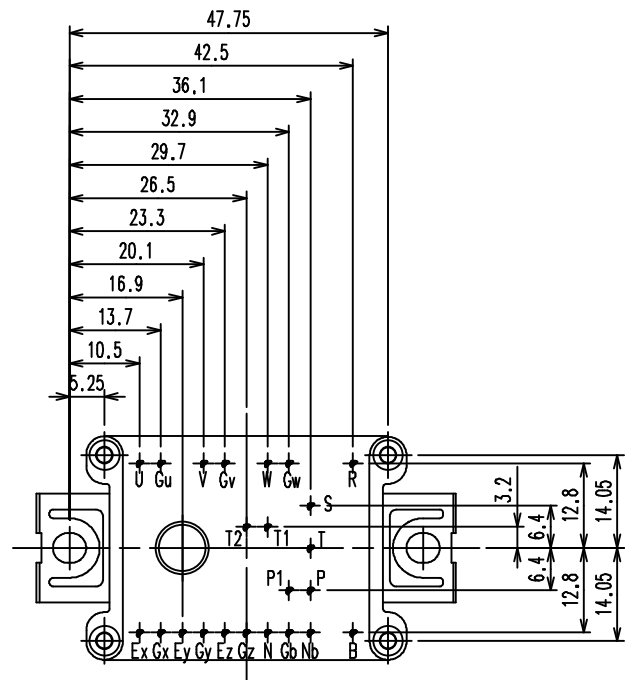
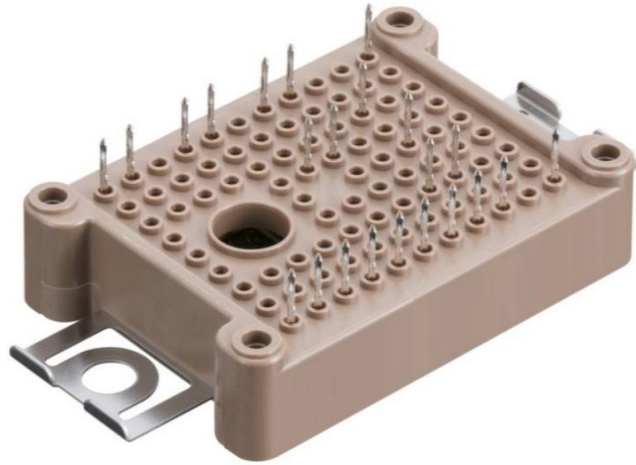
- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

■ **Outline drawing (Unit : mm)**



断面A-A (1.5:1)
SECTION A-A

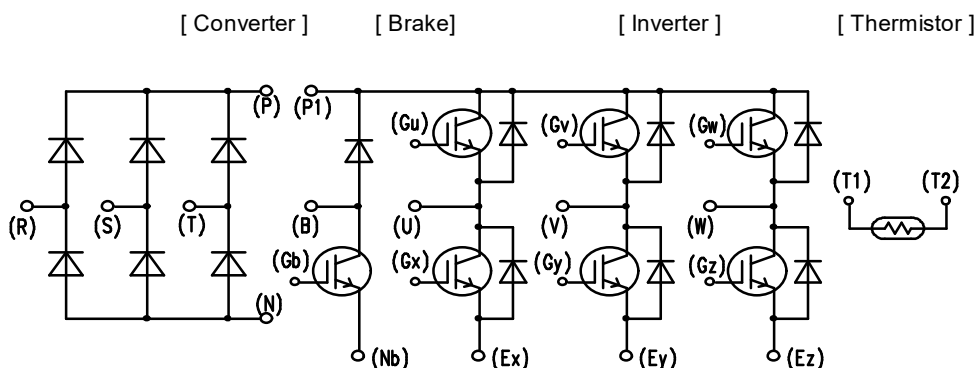
■ **Typical appearance**



ALL DIMENSION IN THE LEFT FIGURE ARE REFERENCE
PIN POSITION TO DESIGNED CENTER OF MODULE ± 0.7
PIN-GRID SPACING 3.2mm

Weight: 25 g (typ.)

■ **Equivalent circuit**



7MBR25XKA120-50

IGBT Modules
■ Maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage, Gate-Emitter short-circuited	V_{CES}		1200	V	
	Gate-Emitter voltage, Collector-Emitter short-circuited	V_{GES}		± 20	V	
	Collector current	I_C	Continuous $T_c=100^\circ\text{C}$	25	A	
	Repetitive peak collector current	I_{CRM}	1ms	40		
	Forward current	I_F	Continuous	25		
	Repetitive peak forward current	I_{FRM}	1ms	40		
	Total power dissipation	P_{tot}	1 device	155	W	
Brake IGBT	Collector-Emitter voltage, Gate-Emitter short-circuited	V_{CES}		1200	V	
	Gate-Emitter voltage, Collector-Emitter short-circuited	V_{GES}		± 20	V	
	Collector current	I_C	Continuous $T_c=100^\circ\text{C}$	25	A	
	Repetitive peak collector current	I_{CRM}	1ms	40		
	Total power dissipation	P_{tot}	1 device	155	W	
Brake FWD	Forward current	I_F	Continuous	10	A	
	Repetitive peak forward current	I_{FRM}	1ms	20		
	Repetitive peak reverse voltage	V_{RRM}		1200	V	
Converter	Repetitive peak reverse voltage	V_{RRM}		1600	V	
	Average output current	I_O	Three-phase full wave rectified current $T_c=80^\circ\text{C}$	25	A	
	Surge forward current (Non-Repetitive) (*1)	I_{FSM}	$t=10\text{ms}$, Half sine wave form	$T_{vj}=25^\circ\text{C}$	350	A
				$T_{vj}=150^\circ\text{C}$	300	
	I^2t (Non-Repetitive) (*1)	I^2t		$T_{vj}=25^\circ\text{C}$	615	A^2s
			$T_{vj}=150^\circ\text{C}$	450		
Virtual junction temperature		T_{vj}	Inverter, Brake	175	$^\circ\text{C}$	
			Converter	150		
Operating virtual junction temperature (under switching conditions)		T_{vjop}	Inverter, Brake	175		
			Converter	150		
Case temperature		T_c		125		
Storage temperature		T_{stg}		-40 ~ 125		
Isolation voltage	Between terminals and copper base (*2) Between thermistor and others (*3)	V_{isol}	A.C. : 1min.	2500	Vrms	
Screw torque	Mounting torque of screws to heat sink	M_s	M4	1.3~1.7	N·m	

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

7MBR25XKA120-50

■ Electrical characteristics (at $T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	-	-	50	μA	
Gate leakage current, Collector-Emitter short-circuited	I_{GES}	$V_{CE} = 0\text{V}$ $V_{GE} = +20/-20\text{V}$	-	-	100	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 25\text{mA}$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 25\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.90	2.40	V
			$T_{vj}=25^{\circ}\text{C}$	-	1.70	2.15	
	$V_{CE(sat)}$ (chip)	$T_{vj}=125^{\circ}\text{C}$	-	2.20	-		
		$T_{vj}=150^{\circ}\text{C}$	-	2.30	-		
		$T_{vj}=175^{\circ}\text{C}$	-	2.40	-		
Internal gate resistance	r_g	-	-	0	-	Ω	
Capacitance	C_{ies}	$V_{CE} = 10\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	2.0	-	nF	
	C_{oes}		-	0.07	-		
	C_{res}		-	0.02	-		
Gate charge	Q_G	$V_{CC} = 600\text{V}$ $V_{GE} = -15 \rightarrow +15\text{V}$ $I_C = 25\text{A}$	-	130	-	nC	
Forward voltage	V_F (terminal)	$I_F = 25\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	2.90	3.40	V
			$T_{vj}=25^{\circ}\text{C}$	-	2.70	3.15	
	V_F (chip)	$T_{vj}=125^{\circ}\text{C}$	-	2.95	-		
		$T_{vj}=150^{\circ}\text{C}$	-	2.90	-		
		$T_{vj}=175^{\circ}\text{C}$	-	2.90	-		
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600\text{V}$ $I_C, I_F = 25\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 20\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.04	-	μs
			$T_{vj}=125^{\circ}\text{C}$	-	0.04	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.04	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.04	-	
	t_r	$V_{CC} = 600\text{V}$ $I_C, I_F = 25\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 20\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.02	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.03	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.03	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.03	-	
	$t_{d(off)}$	$V_{CC} = 600\text{V}$ $I_C, I_F = 25\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 20\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.15	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.19	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.20	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.20	-	
t_f	$V_{CC} = 600\text{V}$ $I_C, I_F = 25\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 20\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.15	-		
		$T_{vj}=125^{\circ}\text{C}$	-	0.17	-		
		$T_{vj}=150^{\circ}\text{C}$	-	0.20	-		
		$T_{vj}=175^{\circ}\text{C}$	-	0.21	-		
Reverse recovery time	t_{rr}	$V_{CC} = 600\text{V}$ $I_C, I_F = 25\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 20\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.06	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.11	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.13	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.16	-	

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

7MBR25XKA120-50

IGBT Modules

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Inverter Switching loss (per pulse)	E_{on}	$V_{CC} = 600V$ $I_C, I_F = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	1.51	-	mJ
			$T_{vj} = 125^\circ C$	-	1.95	-	
			$T_{vj} = 150^\circ C$	-	2.07	-	
			$T_{vj} = 175^\circ C$	-	2.19	-	
	E_{off}	$V_{CC} = 600V$ $I_C, I_F = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	1.79	-	
			$T_{vj} = 125^\circ C$	-	2.30	-	
			$T_{vj} = 150^\circ C$	-	2.43	-	
			$T_{vj} = 175^\circ C$	-	2.54	-	
	E_{rr}	$V_{CC} = 600V$ $I_C, I_F = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	1.00	-	
			$T_{vj} = 125^\circ C$	-	1.27	-	
			$T_{vj} = 150^\circ C$	-	1.47	-	
			$T_{vj} = 175^\circ C$	-	1.66	-	
Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 1200V$	-	-	50	μA	
Gate leakage current, Collector-Emitter short-circuited	I_{GES}	$V_{CE} = 0V, \quad V_{GE} = +20/-20V$	-	-	100	nA	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 25A$	$T_{vj} = 25^\circ C$	-	1.90	2.40	V
			$T_{vj} = 25^\circ C$	-	1.70	2.15	
	$V_{CE(sat)}$ (chip)		$T_{vj} = 125^\circ C$	-	2.20	-	
			$T_{vj} = 175^\circ C$	-	2.30	-	
Internal gate resistance	r_g	-	-	0	-	Ω	
Brake Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600V$ $I_C = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	0.04	-	μs
			$T_{vj} = 125^\circ C$	-	0.04	-	
			$T_{vj} = 150^\circ C$	-	0.04	-	
			$T_{vj} = 175^\circ C$	-	0.04	-	
	t_r	$V_{CC} = 600V$ $I_C = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	0.02	-	
			$T_{vj} = 125^\circ C$	-	0.03	-	
			$T_{vj} = 150^\circ C$	-	0.03	-	
			$T_{vj} = 175^\circ C$	-	0.03	-	
	$t_{d(off)}$	$V_{CC} = 600V$ $I_C = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	0.15	-	
			$T_{vj} = 125^\circ C$	-	0.19	-	
			$T_{vj} = 150^\circ C$	-	0.20	-	
			$T_{vj} = 175^\circ C$	-	0.20	-	
	t_f	$V_{CC} = 600V$ $I_C = 25A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 20 \Omega$	$T_{vj} = 25^\circ C$	-	0.15	-	
			$T_{vj} = 125^\circ C$	-	0.17	-	
			$T_{vj} = 150^\circ C$	-	0.20	-	
			$T_{vj} = 175^\circ C$	-	0.21	-	
Reverse current	I_{RRM}	$V_R = 1200V$	-	-	50	μA	
Forward voltage	V_F (terminal)	$I_F = 10A$	$T_j = 25^\circ C$	-	2.10	2.60	V
			$T_j = 25^\circ C$	-	1.90	2.35	
	V_F (chip)		$T_{vj} = 125^\circ C$	-	1.95	-	
			$T_{vj} = 175^\circ C$	-	1.90	-	
Converter Reverse current	I_{RRM}	$V_R = 1600V$	-	-	50	μA	
			terminal	-	1.25	1.75	V
Thermistor Resistance	R	$T = 25^\circ C$	-	5000	-	Ω	
		$T = 100^\circ C$	465	495	520		
	B value	B	$T = 25/50^\circ C$	3305	3375	3450	K

 (*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

7MBR25XKA120-50

NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

■ Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance junction to case (1 device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.94	K/W
		Inverter FWD	-	-	1.75	
		Brake IGBT	-	-	0.94	
		Brake FWD	-	-	1.75	
		Converter Diode	-	-	0.97	
Thermal resistance case to heat sink(*1) (1 device)	$R_{th(c-s)}$	Inverter IGBT	-	0.74	-	
		Inverter FWD	-	0.92	-	
		Brake IGBT	-	0.78	-	
		Brake FWD	-	0.75	-	
		Converter Diode	-	0.78	-	

(*1) This is the value which is defined mounting on the additional cooling fin with 1 W/(m·K) thermal grease.

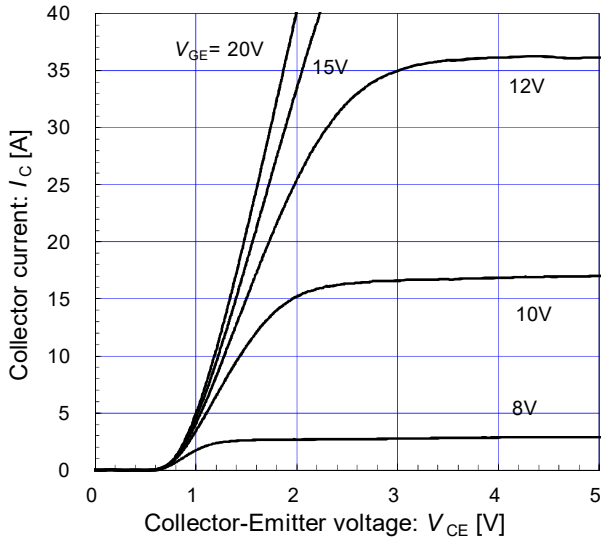
7MBR25XKA120-50

IGBT Modules

[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

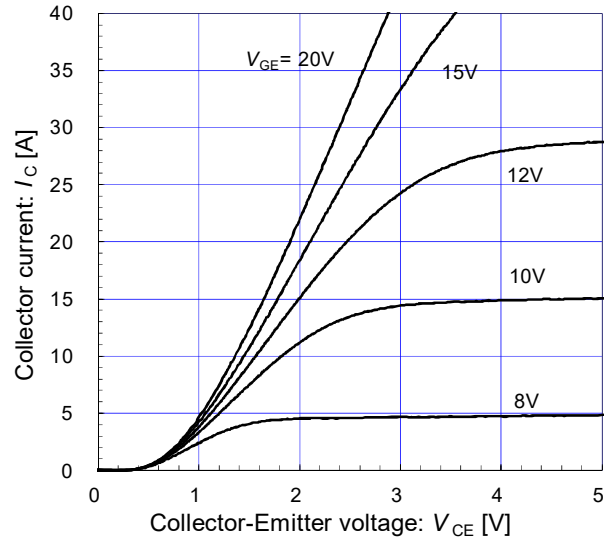
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

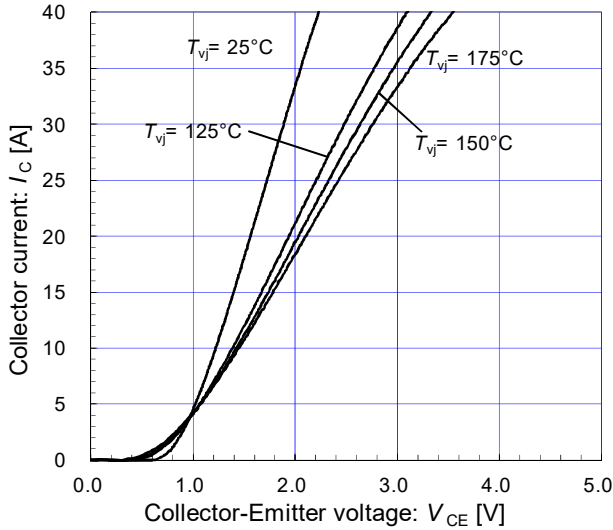
$T_{vj} = 175^{\circ}\text{C}$ / chip



[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

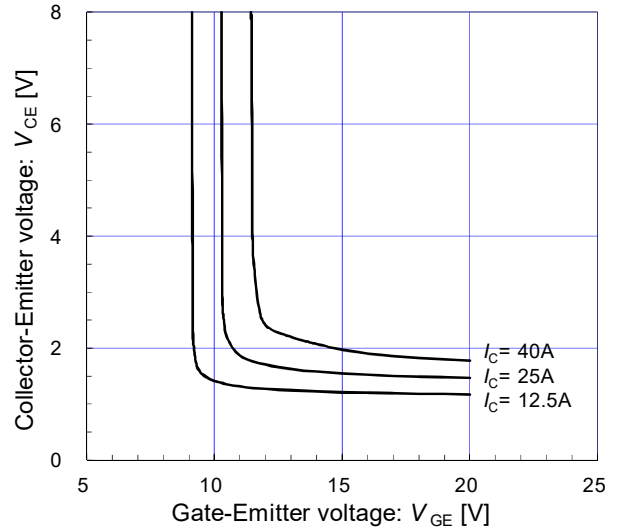
$V_{GE} = 15\text{V}$ / chip



[Inverter]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)

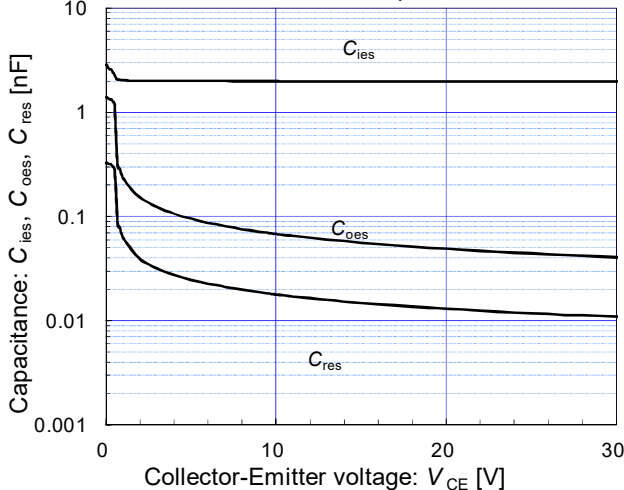
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Inverter]

Capacitance vs. Collector-Emittor voltage (typ.)

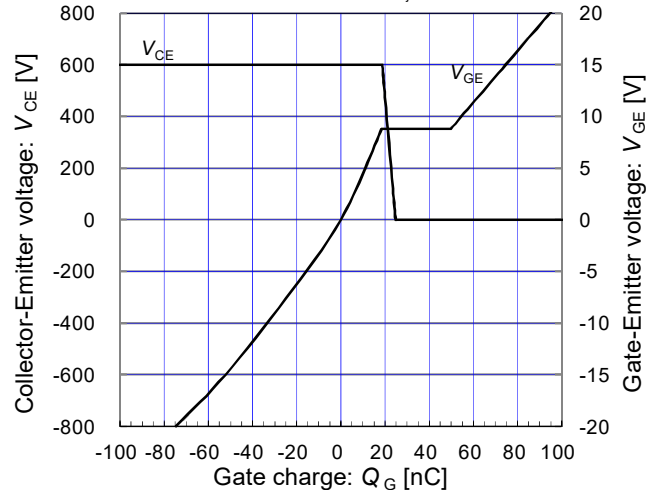
$V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_{vj} = 25^{\circ}\text{C}$



[Inverter]

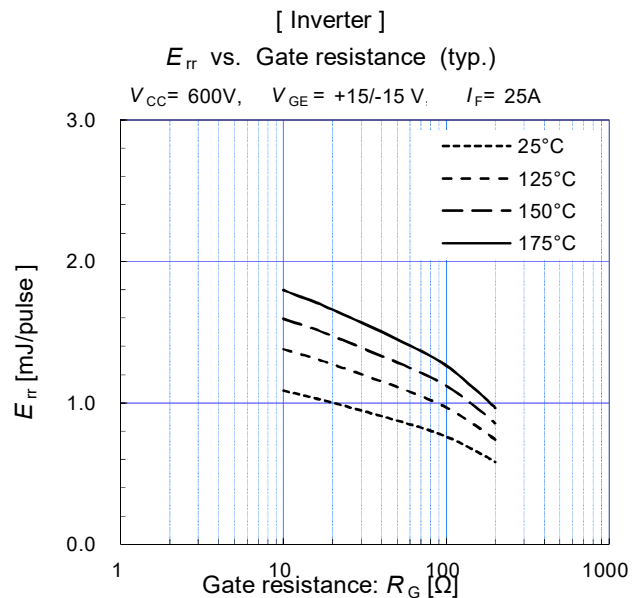
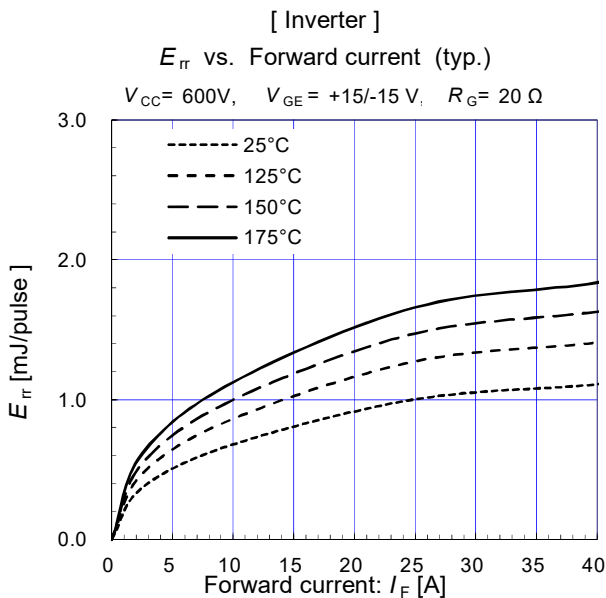
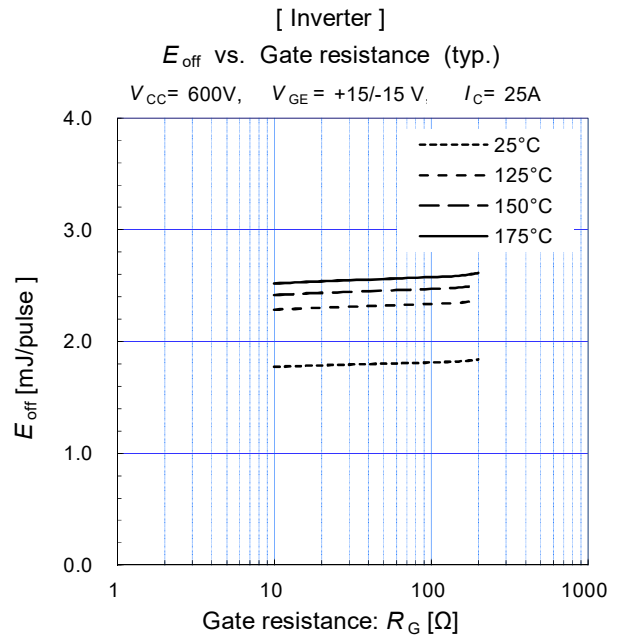
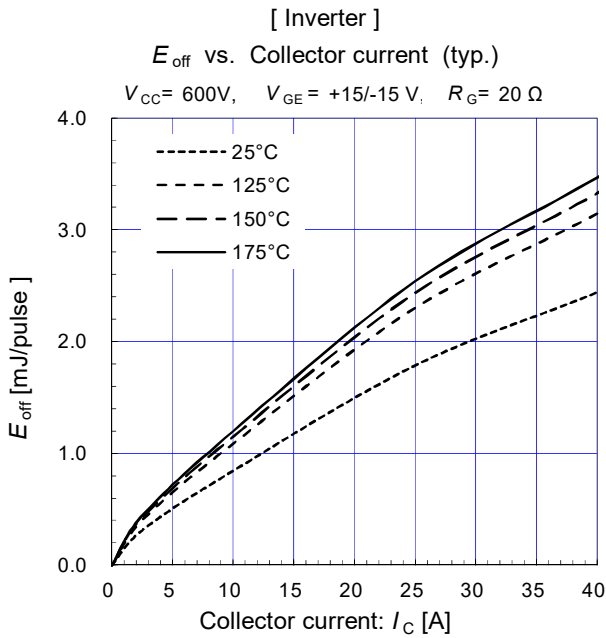
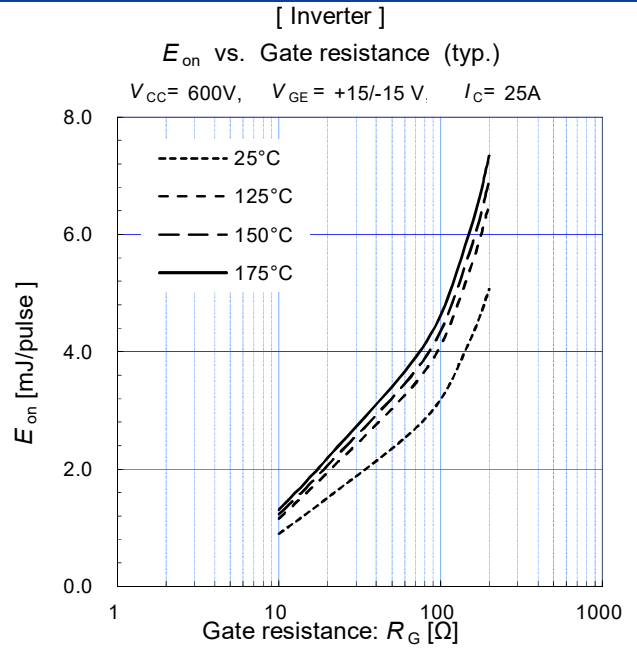
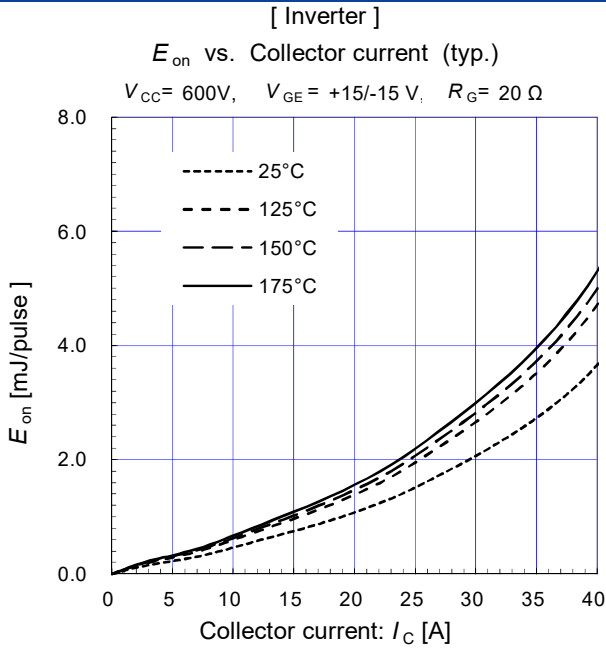
Dynamic gate charge (typ.)

$V_{CC} = 600\text{V}$, $I_C = 25\text{A}$, $T_{vj} = 25^{\circ}\text{C}$



7MBR25XKA120-50

IGBT Modules



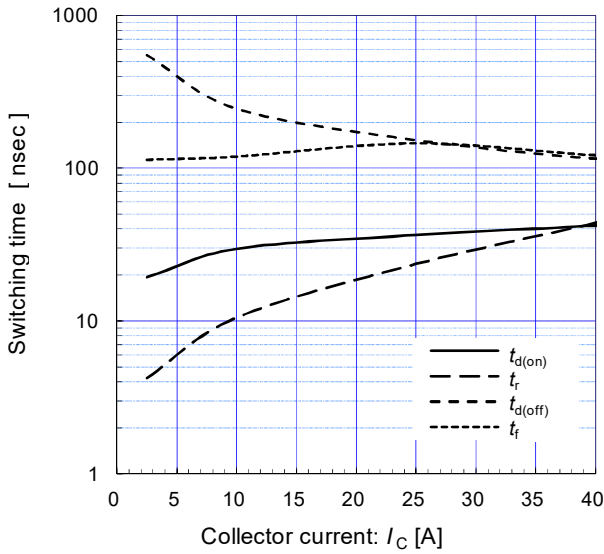
7MBR25XKA120-50

IGBT Modules

[Inverter]

Switching time vs. Collector current (typ.)

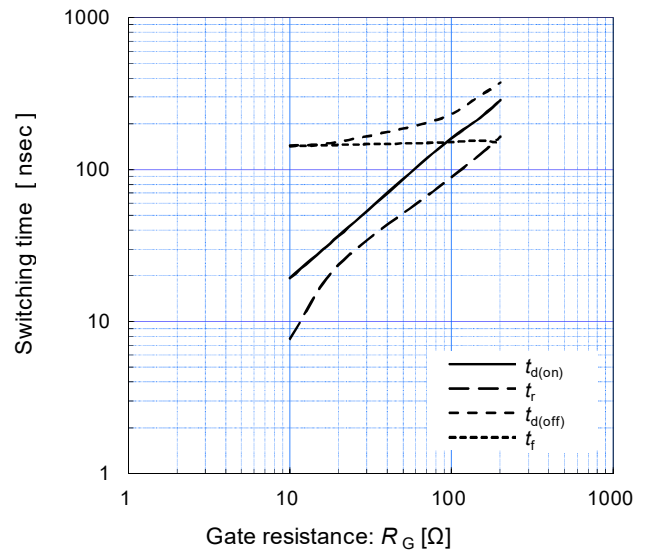
$V_{CC}=600V, R_G=20\Omega, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

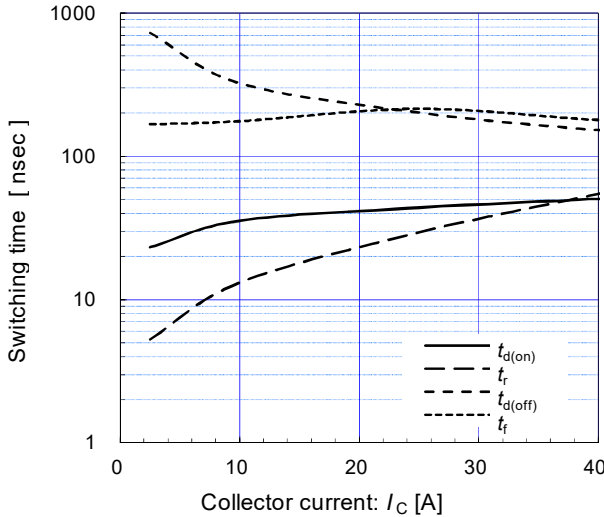
$V_{CC}=600V, I_C=25A, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

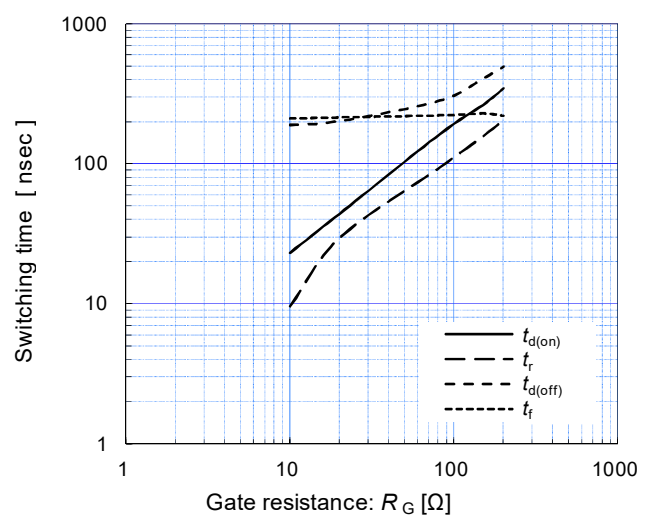
$V_{CC}=600V, R_G=20\Omega, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

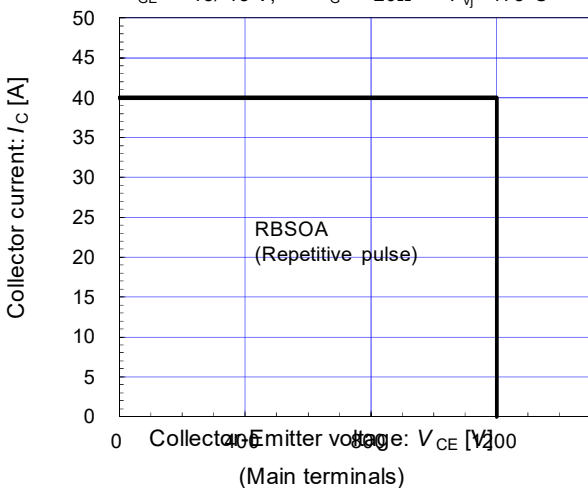
$V_{CC}=600V, I_C=25A, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Reverse bias safe operating area (max.)

$V_{GE}=+15/-15V, R_G \geq 20\Omega, T_{vj}=175^\circ C$

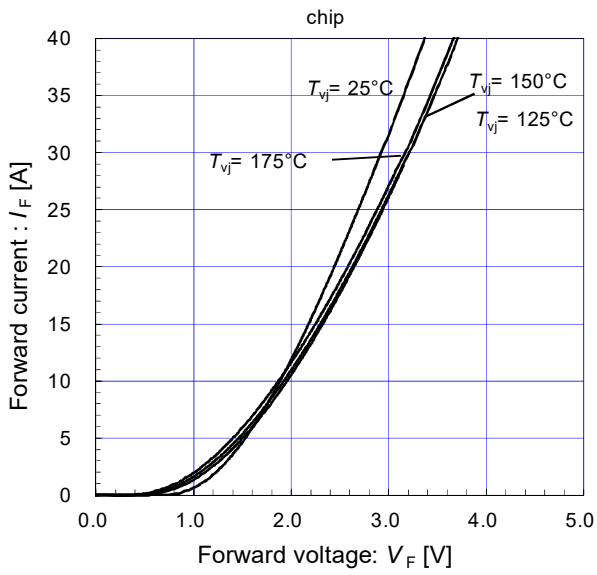


7MBR25XKA120-50

IGBT Modules

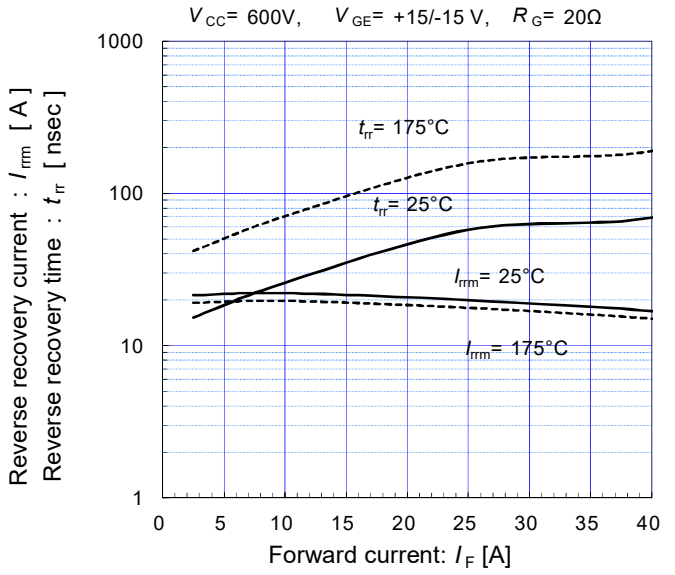
[Inverter]

Forward current vs. Forward voltage (typ.)



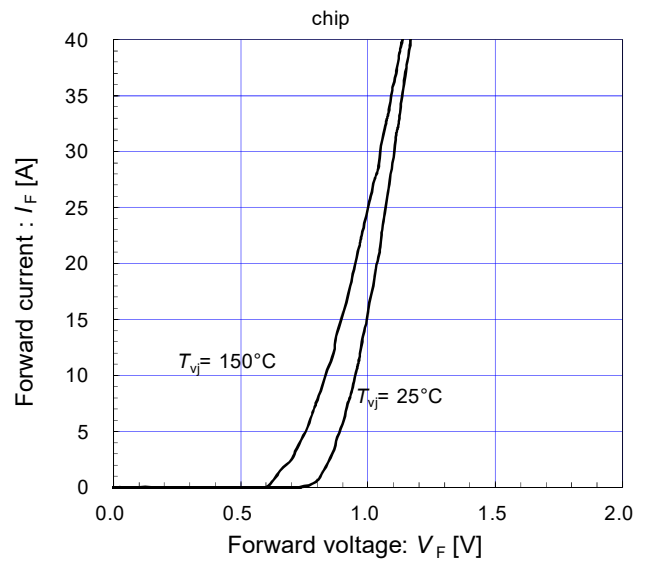
[Inverter]

Reverse recovery characteristics (typ.)

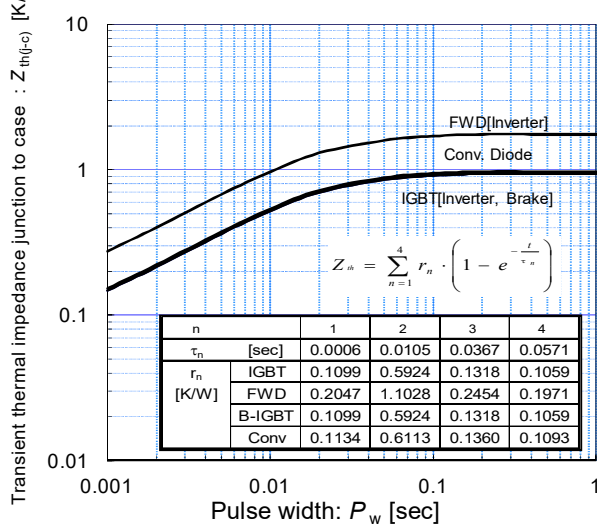


[Converter]

Forward current vs. Forward voltage (typ.)

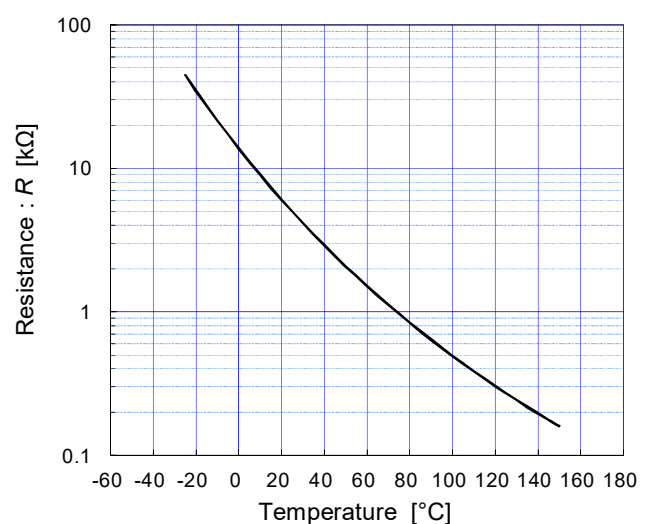


Transient thermal impedance (max.)



[Thermistor]

Temperature characteristic (typ.)

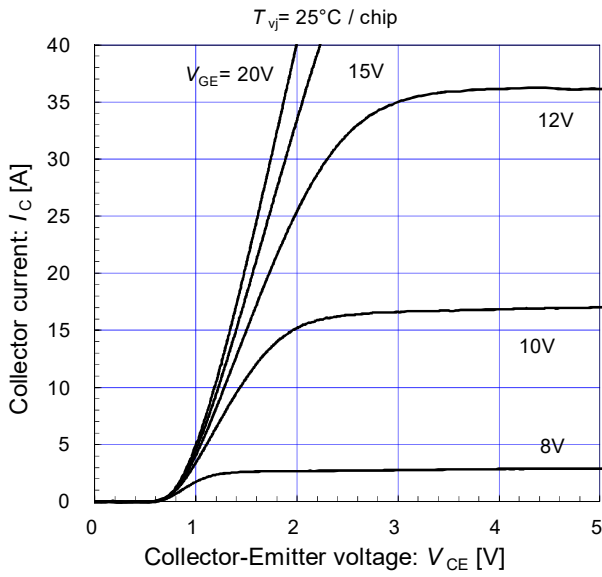


7MBR25XKA120-50

IGBT Modules

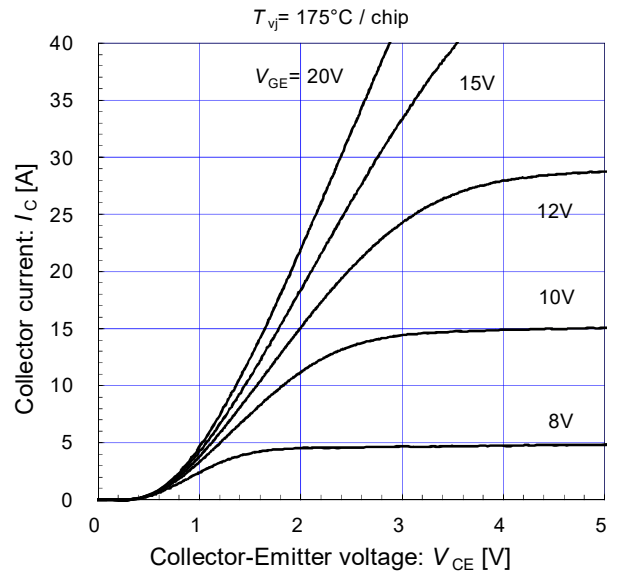
[Brake]

Collector current vs. Collector-Emmitter voltage (typ.)



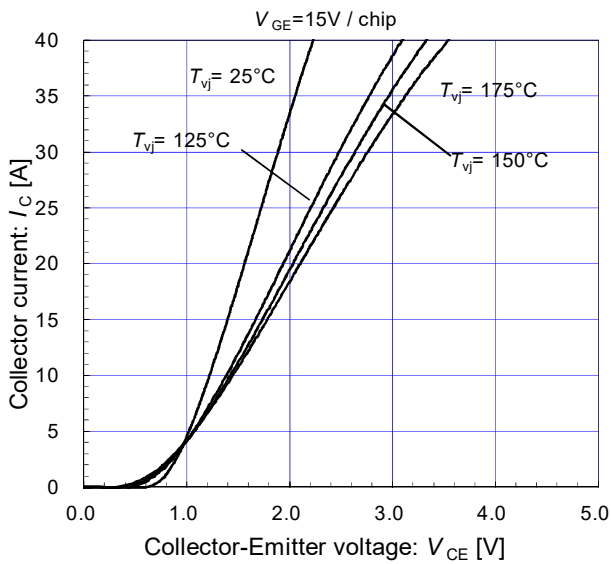
[Brake]

Collector current vs. Collector-Emmitter voltage (typ.)



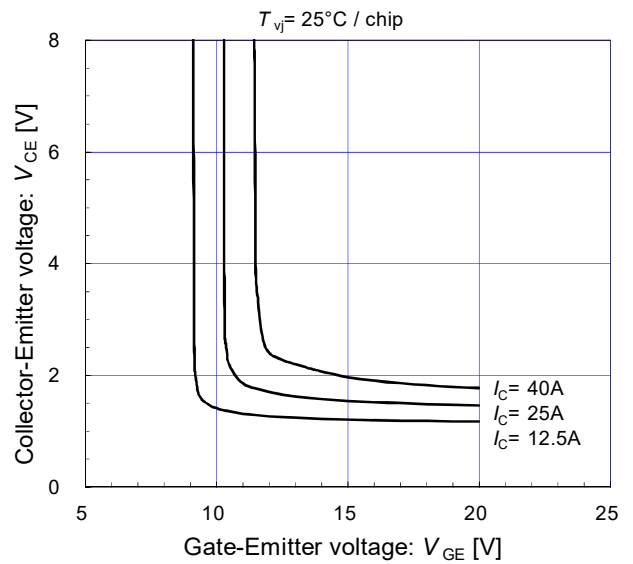
[Brake]

Collector current vs. Collector-Emmitter voltage (typ.)



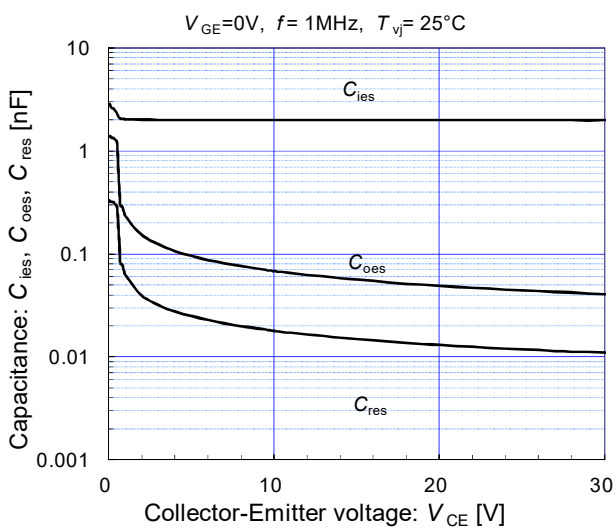
[Brake]

Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)



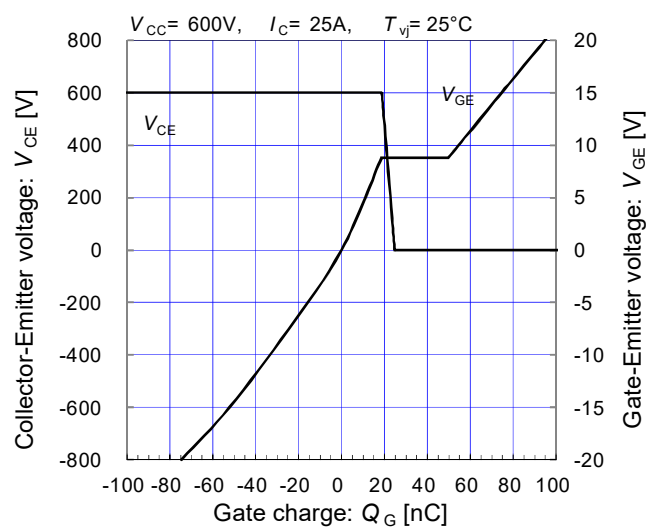
[Brake]

Capacitance vs. Collector-Emmitter voltage (typ.)



[Brake]

Dynamic gate charge (typ.)



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